REMARKS

Claims 1-7 are pending in the present application.

Entry of the above amendments is earnestly solicited. An early and favorable first action on the merits is earnestly requested.

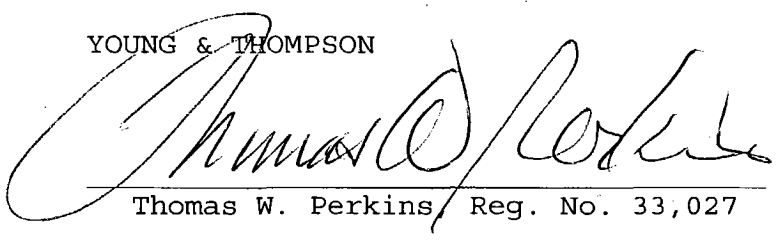
Should there be any matters that need to be resolved in the present application, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

YOUNG & THOMPSON



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TWP/maf
Attachments

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

The paragraph beginning on pages 2-3, line 13, has been amended as follows:

--In a [damascenel] damascene method widely used for forming the interconnect by using the copper as the interconnect material, trenches formed in the interlayer dielectric film are filled with a barrier metal and the copper, and the surplus copper and the surplus barrier metal on the dielectric film are removed by the chemical mechanical polishing to form the interconnect. In the current [damascenel] damascene method, since the copper easily reacts with the SiO_2 and diffuses during the formation of the interlayer dielectric film after the [damascenel] damascene interconnect formation, a cap dielectric film made of SiN for the copper having a thickness of about 50 to 100 nm is formed by the plasma CVD using the SiH_4, NH_3 and N_2. Thereafter, the interlayer dielectric film made of SiO_2 is formed.--.

The paragraph beginning on page 8, line 11, has been amended as follows:

--In a second embodiment, a SiN film was formed in accordance with procedures sequentially shown in Fig. 3A to [2]3F.--.